

ABSTRACT OF THE INVENTION

The invention provides a method for fabricating a semiconductor device including a concaved capacitor device having a lower electrode, a capacitor dielectric film of a perovskite type high dielectric constant or ferroelectric material formed on the lower electrode and an upper electrode formed on the capacitor dielectric film. In this method, a step of forming a conducting film to be formed into the lower electrode includes sub-steps of forming a lower conducting film by sputtering on walls and a bottom of a recess formed in an insulating film on a substrate; and forming an upper conducting film on the lower conducting film by CVD.

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